

## 1. General description

Planar passivated Silicon Controlled Rectifier with ultra-sensitive gate in a SOT54 (TO-92) plastic package.

## 2. Features and benefits

- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Ultra sensitive gate

## 3. Applications

- Electronic ballasts
- Safety shut down and protection circuits
- Sensing circuits
- Smoke detectors
- Switched Mode Power Supplies

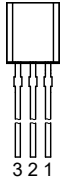

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	-	600	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{lead} \leq 67\text{ °C}$ ; <a href="#">Fig. 1</a>	-	-	0.51	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{lead} \leq 67\text{ °C}$ ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	0.8	A
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 10\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	8	A
		half sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 8.3\text{ ms}$	-	-	9	A
$T_j$	junction temperature		-	-	125	°C
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 10\text{ mA}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	0.5	-	7	$\mu\text{A}$
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$ ; $T_j = 125\text{ °C}$ ; $R_{GK} = 1\text{ k}\Omega$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>	75	-	-	$\text{V}/\mu\text{s}$

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A	anode	 <p>TO-92 (SOT54)</p>	
2	G	gate		
3	K	cathode		

## 6. Ordering information

Table 3. Ordering information

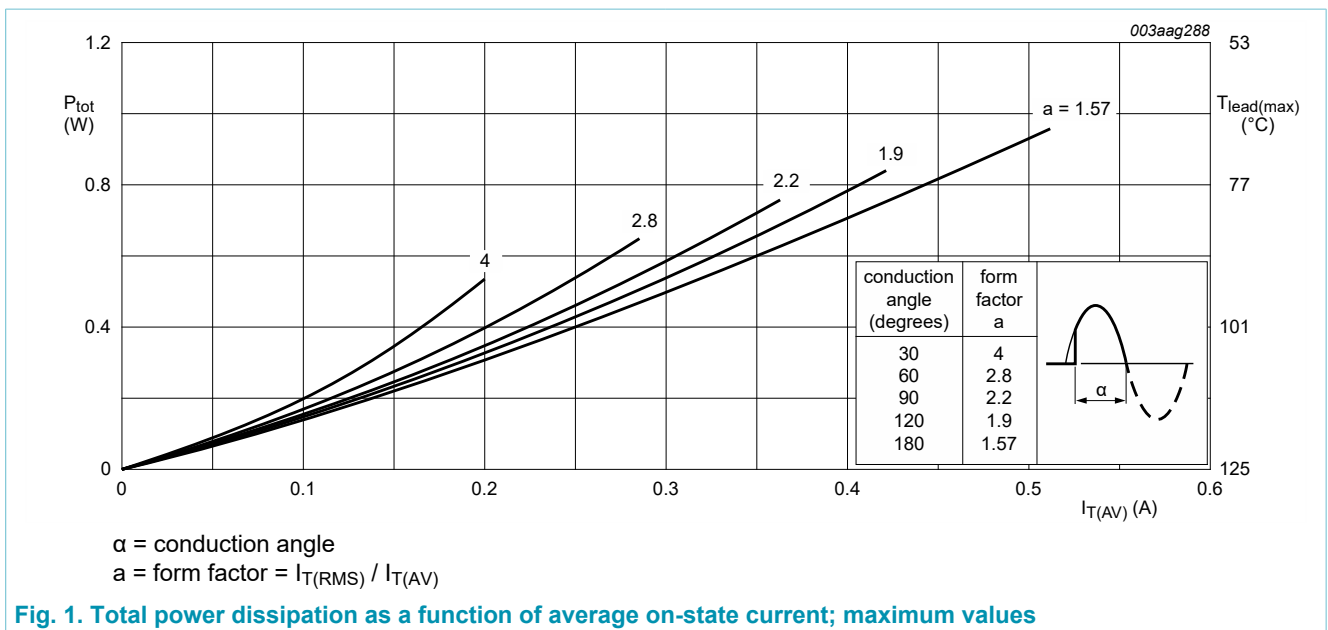
Type number	Package		
	Name	Description	Version
N0118GA	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

## 7. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
$V_{RRM}$	repetitive peak reverse voltage		-	600	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{lead} \leq 67\text{ }^{\circ}\text{C}$ ; Fig. 1	-	0.51	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{lead} \leq 67\text{ }^{\circ}\text{C}$ ; Fig. 2; Fig. 3	-	0.8	A
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 10\text{ ms}$ ; Fig. 4; Fig. 5	-	8	A
		half sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 8.3\text{ ms}$	-	9	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; SIN	-	0.32	$\text{A}^2\text{s}$
$di_T/dt$	rate of rise of on-state current	$I_T = 0.8\text{ A}$ ; $I_G = 10\text{ mA}$ ; $di_G/dt = 0.1\text{ A}/\mu\text{s}$	-	50	$\text{A}/\mu\text{s}$
$I_{GM}$	peak gate current		-	1	A
$V_{RGM}$	peak reverse gate voltage		-	5	V
$P_{GM}$	peak gate power		-	2	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
$T_{stg}$	storage temperature		-40	150	$^{\circ}\text{C}$
$T_j$	junction temperature		-	125	$^{\circ}\text{C}$



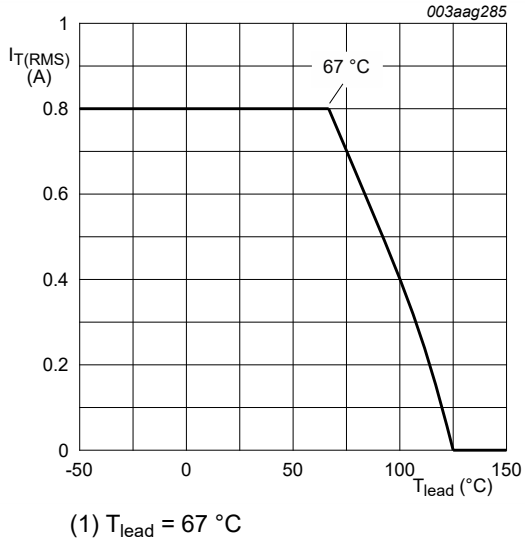


Fig. 2. RMS on-state current as a function of lead temperature; maximum values

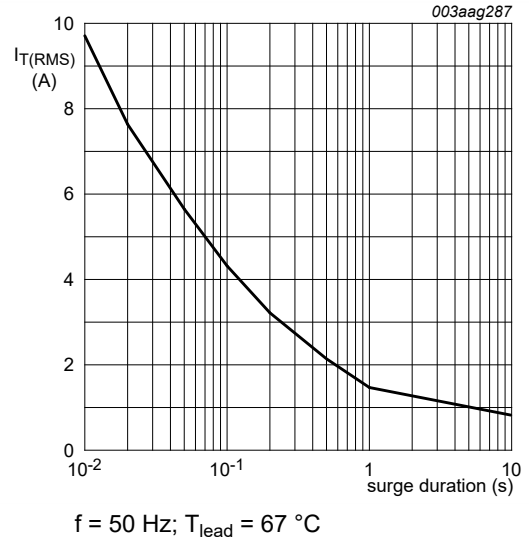


Fig. 3. RMS on-state current as a function of surge duration; maximum values

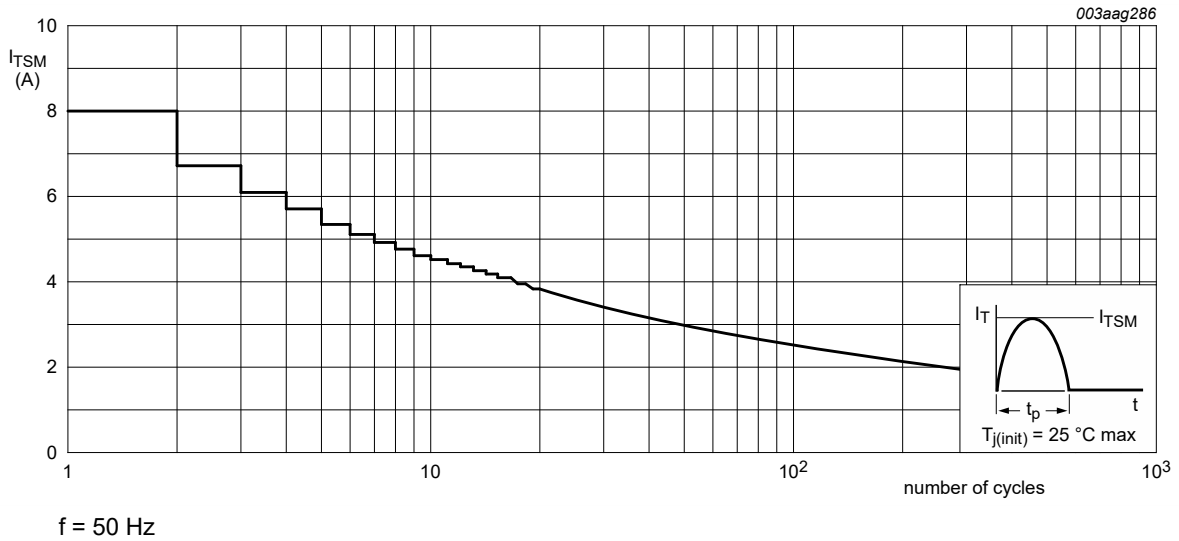
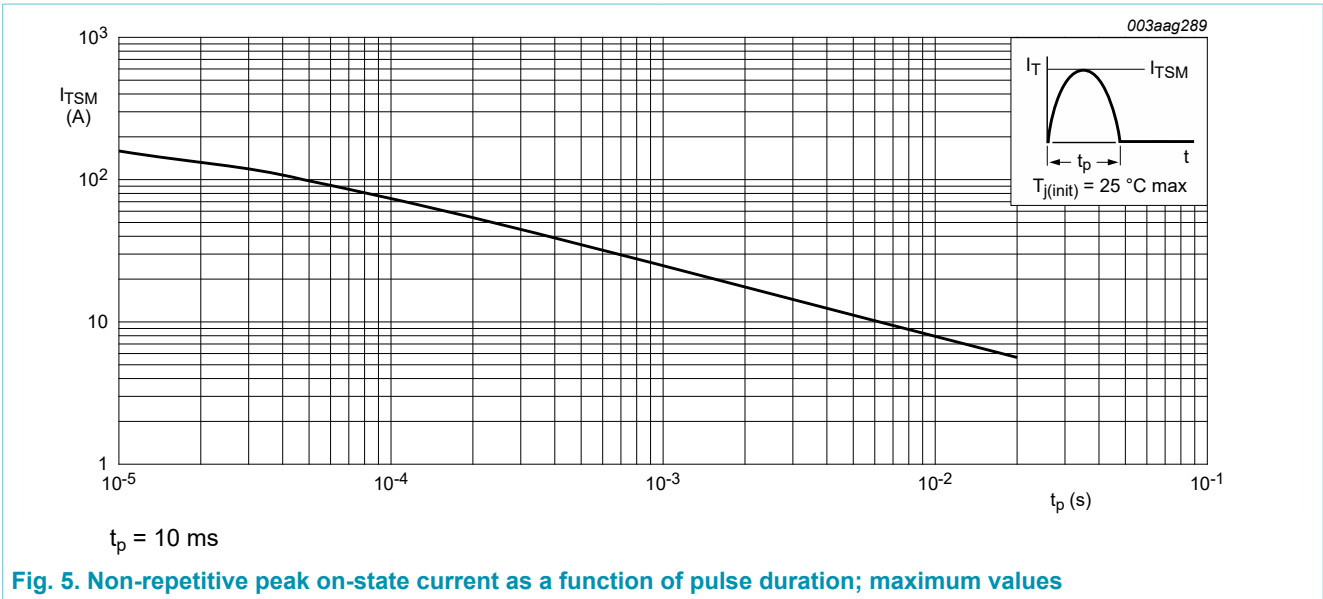


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



## 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	<a href="#">Fig. 6</a>	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W

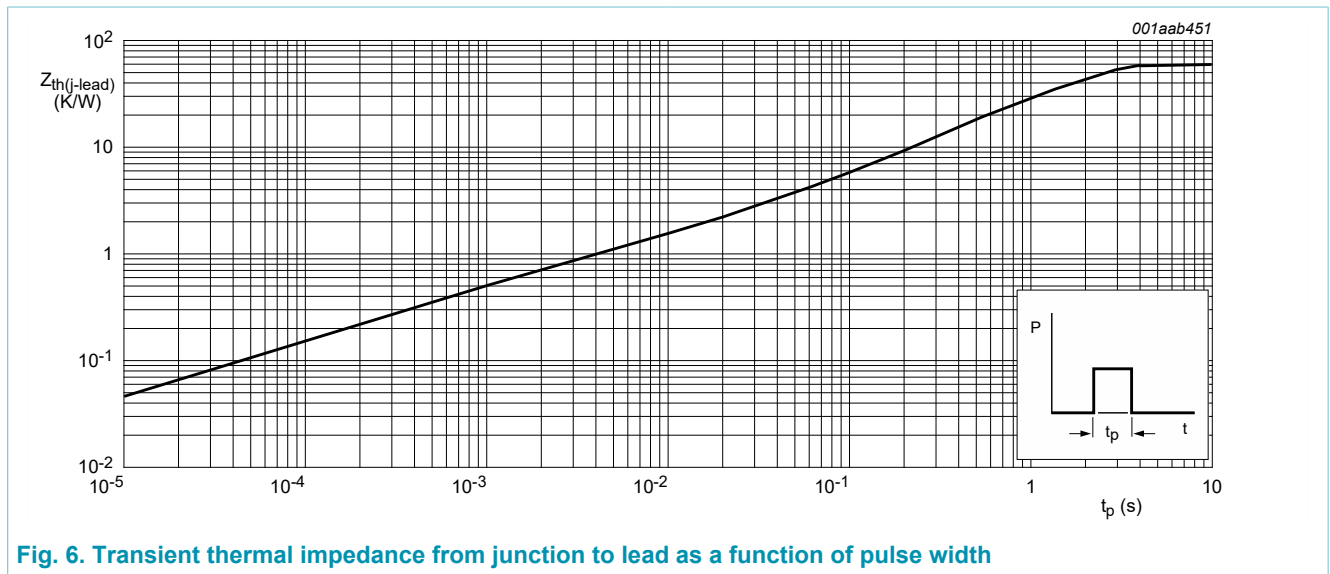
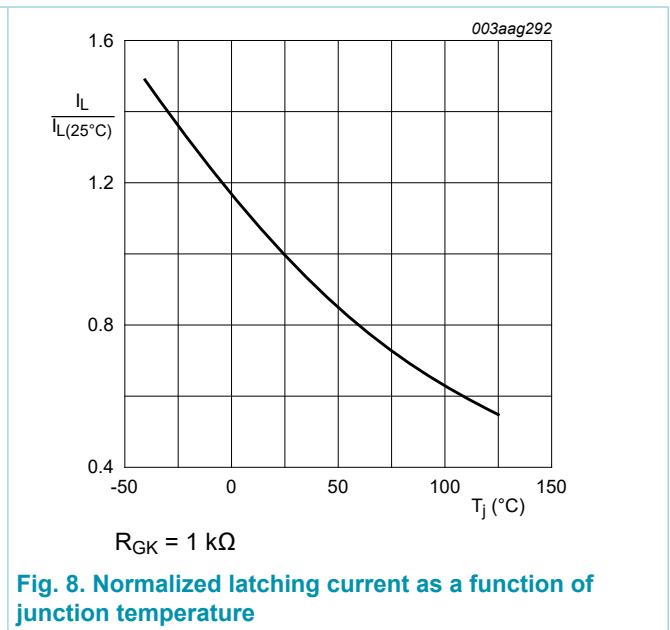
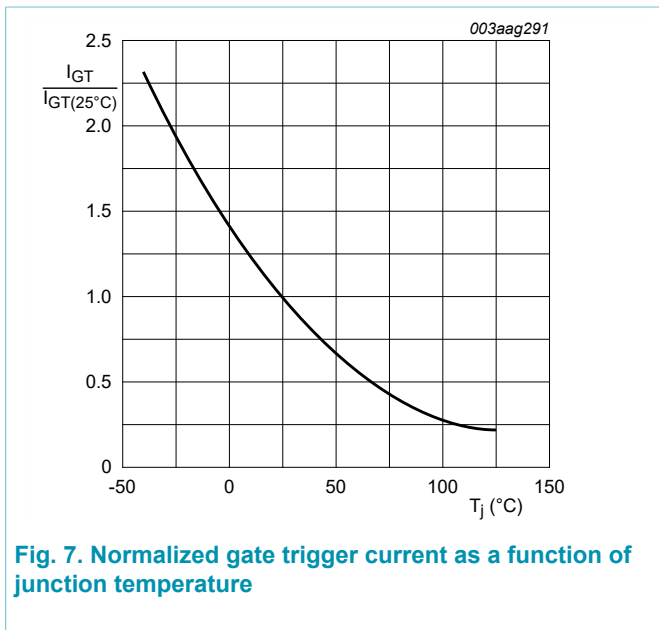


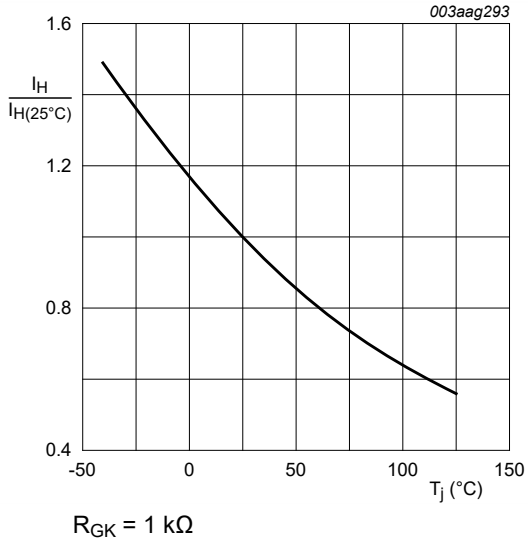
Fig. 6. Transient thermal impedance from junction to lead as a function of pulse width

## 9. Characteristics

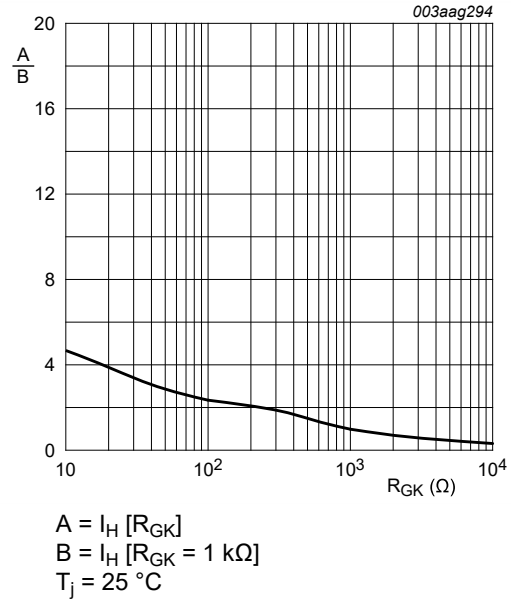
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 10\text{ mA}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>	0.5	-	7	$\mu\text{A}$
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>	-	-	6	$\text{mA}$
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a> ; <a href="#">Fig. 10</a>	-	-	5	$\text{mA}$
$V_T$	on-state voltage	$I_T = 1.6\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>	-	1.4	1.95	$\text{V}$
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>	-	-	0.8	$\text{V}$
$I_D$	off-state current	$V_D = 400\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$	-	-	10	$\mu\text{A}$
		$V_D = 600\text{ V}$ ; $R_{GK(\text{ext})} = 1\text{ k}\Omega$ ; $T_j = 125\text{ }^\circ\text{C}$	-	-	100	$\mu\text{A}$
$I_R$	reverse current	$V_R = 600\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; $R_{GK(\text{ext})} = 1\text{ k}\Omega$	-	-	10	$\mu\text{A}$
		$V_R = 600\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $R_{GK(\text{ext})} = 1\text{ k}\Omega$	-	-	100	$\mu\text{A}$
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $R_{GK} = 1\text{ k}\Omega$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>	75	-	-	$\text{V}/\mu\text{s}$

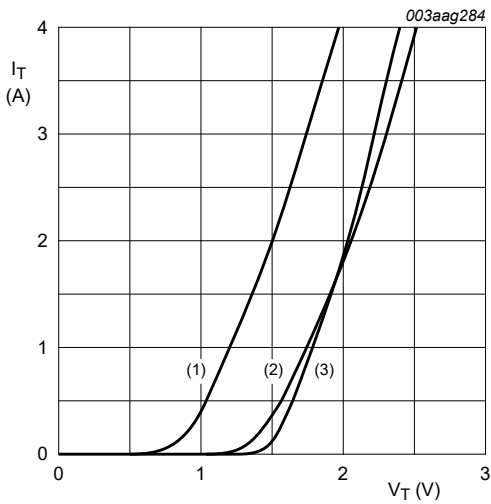




**Fig. 9. Normalized holding current as a function of junction temperature**

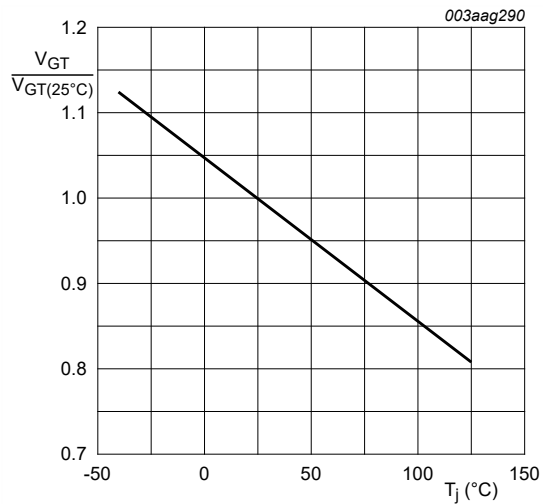


**Fig. 10. Normalized holding current as a function of gate-cathode resistance (typical values)**



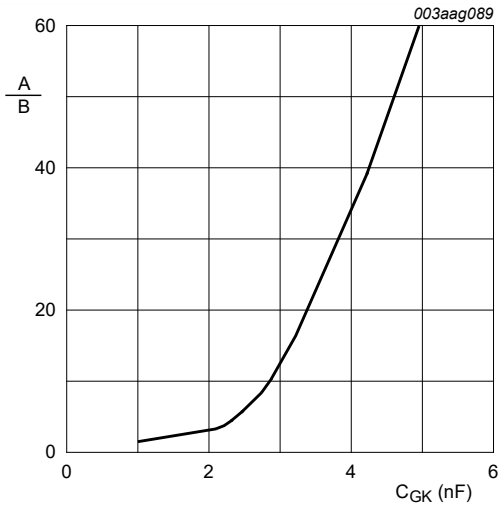
$V_o = 1.383 \text{ V}; R_s = 0.4 \text{ } \Omega$   
 (1)  $T_j = 125 \text{ } ^\circ\text{C}$ ; typical values  
 (2)  $T_j = 125 \text{ } ^\circ\text{C}$ ; maximum values  
 (3)  $T_j = 25 \text{ } ^\circ\text{C}$ ; maximum values

**Fig. 11. On-state current as a function of on-state voltage**



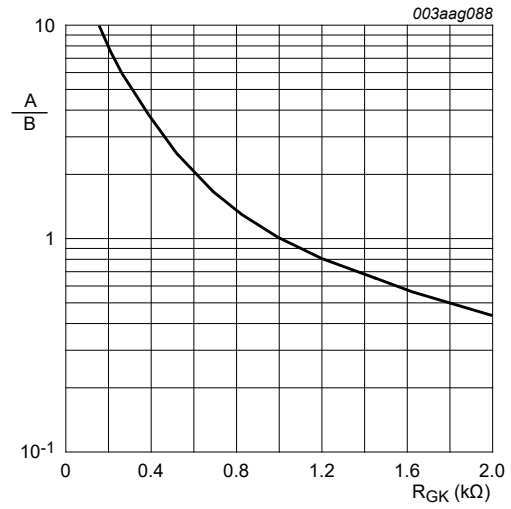
**Fig. 12. Normalized gate trigger voltage as a function of junction temperature**





A = dV / dt [CGK]  
 B = dV / dt [R<sub>GK</sub> = 1 kΩ]  
 T<sub>j</sub> = 125 °C;  
 R<sub>GK</sub> = 1 kΩ; V<sub>DM</sub> = 402 V

Fig. 13. Normalized dVd/dt immunity as a function of gate-cathode capacitance (typical values)



A = dV / dt [CGK]  
 B = dV / dt [R<sub>GK</sub> = 1 kΩ]  
 T<sub>j</sub> = 125 °C;  
 R<sub>GK</sub> = 1 kΩ; V<sub>DM</sub> = 402 V

Fig. 14. Normalized dVd/dt immunity as a function of gate-cathode resistance (typical values)

### 10. Package outline

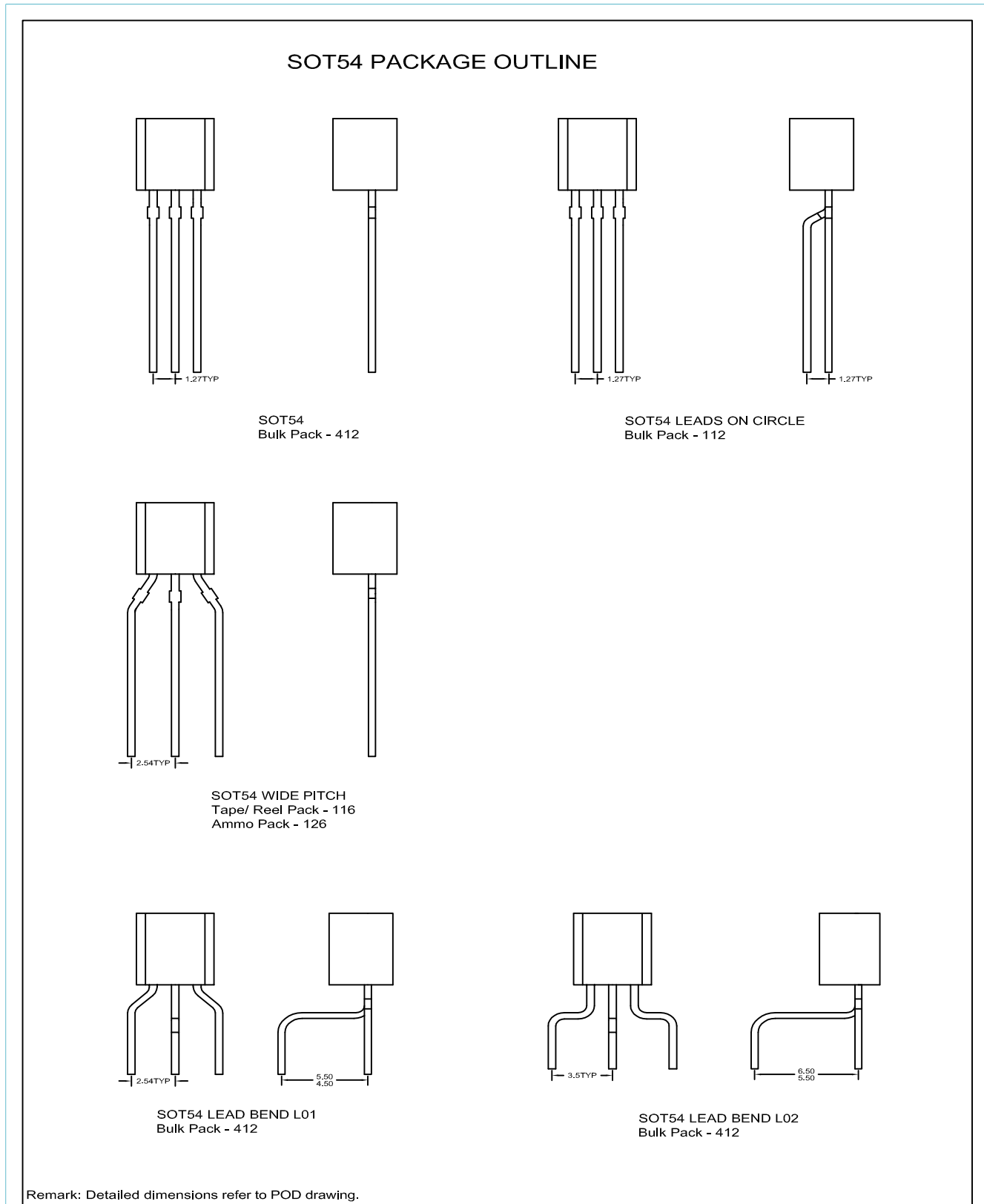


Fig. 15. Package outline TO-92 (SOT54)

# 11. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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